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(54) MASK AND METAL WIRING OF A SEMICONDUCTOR DEVICE FORMED USING THE SAME

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(57) ABSTRACT

A mask including a mask substrate including a cell exposure region and a peripheral exposure region, the cell exposure region configured to expose a metal layer in a cell region of a semiconductor device, the peripheral exposure region configured to expose a metal layer in a peripheral region of the semiconductor device, a first mask pattern configured to expose the metal layer in the peripheral exposure region of the mask substrate to form a signal metal pattern, and a second mask pattern configured to expose the metal layer in the peripheral exposure region of the mask substrate to form a dummy metal pattern, the second mask pattern being adjacent to the first mask pattern, and the second mask pattern having a substantially same width as a width of the first mask pattern may be provided.

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